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N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| BV _{DSS} | R _{DS(ON)} max | I_D max $T_A = +25$ °C |
|-------------------|--------------------------------|-----------------------------|
| 20V | 110mΩ @ V _{GS} = 4.5V | 2A |
| | 145mΩ @ V _{GS} = 2.5V | 1.7A |
| | 230mΩ @ V _{GS} = 1.8V | 1.3A |

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(on)})$ and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

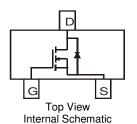
- General Purpose Interfacing Switch
- Power Management Functions
- Boost Application
- Analog Switch

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.008 grams (Approximate)



Top View



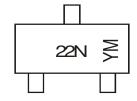
Ordering Information (Note 4)

| Part Number | Case | Packaging |
|--------------|-------|--------------------|
| DMN2230UQ-7 | SOT23 | 3,000/Tape & Reel |
| DMN2230UQ-13 | SOT23 | 10,000/Tape & Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



22N = Marking Code YM = Date Code Marking Y = Year (ex: U = 2007) M = Month (ex: 9 = September)

Date Code Key

| Year | 2007 | 2008 | 2009 | 2010 | 201 | 1 20 | 12 | 2013 | 2014 | 2015 | 2016 | 2017 |
|-------|------|------|-------|------|-------|------|-----|------|------|------|------|------|
| Code | U | V | W | Х | Υ | - 4 | 7 | Α | В | С | D | E |
| Month | Jan | Feb | Mar | Apr | Mav | lun | Jul | Aug | Sep | Oct | Nov | Dec |
| WOITH | Jan | 1 60 | iviai | Apı | iviay | Jun | Jui | Aug | Jep | OCI | 1404 | Dec |



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Units |
|-------------------------------|-----------------|-------|-------|
| Drain-Source Voltage | V_{DSS} | 20 | V |
| Gate-Source Voltage | V_{GSS} | ±12 | V |
| Drain Current (Note 6) | I _D | 2.0 | Α |
| Pulsed Drain Current (Note 7) | I _{DM} | 7 | Α |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Units |
|---|---------------------|-------------|-------|
| Total Power Dissipation (Note 6) | P_{D} | 600 | mW |
| Thermal Resistance, Junction to Ambient | $R_{	hetaJA}$ | 208 | °C/W |
| Operating and Storage Temperature Range | T_{J} , T_{STG} | -55 to +150 | °C |

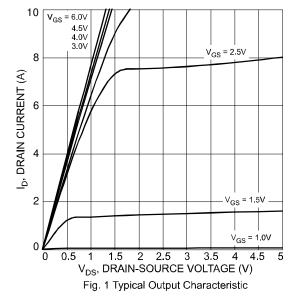
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

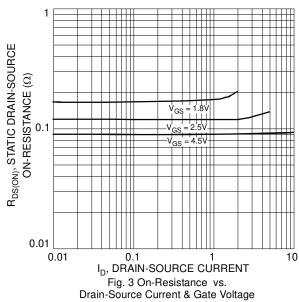
| | • | | | | | |
|-----------------------------------|----------------------|-----|------|-----|------|---|
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
| OFF CHARACTERISTICS (Note 8) | | | | | | |
| Drain-Source Breakdown Voltage | BV_DSS | 20 | _ | | V | $V_{GS} = 0V, I_D = 10\mu A$ |
| Zero Gate Voltage Drain Current | I _{DSS} | _ | _ | 1 | μΑ | $V_{DS} = 20V, V_{GS} = 0V$ |
| Gate-Source Leakage | | _ | _ | ±10 | μΑ | $V_{GS} = \pm 12V, V_{DS} = 0V$ |
| ON CHARACTERISTICS (Note 8) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | 0.5 | _ | 1.0 | V | $V_{DS} = V_{CS}, I_D = 250 \mu A$ |
| | | | 81 | 110 | | $V_{GS} = 4.5V, I_D = 2.5A$ |
| Static Drain-Source On-Resistance | R _{DS} (ON) | _ | 113 | 145 | mΩ | $V_{GS} = 2.5V, I_D = 1.5A$ |
| | | | 170 | 230 | | $V_{GS} = 1.8V, I_D = 1.0A$ |
| Forward Transfer Admittance | Y _{fs} | _ | 5 | | S | $V_{DS} = 5V, I_D = 2.4A$ |
| Diode Forward Voltage (Note 8) | V_{SD} | | 0.8 | 1.1 | > | $V_{GS} = 0V, I_S = 1.05A$ |
| DYNAMIC CHARACTERISTICS | | | | | | |
| Input Capacitance | C _{iss} | _ | 188 | _ | рF | 101/11/ |
| Output Capacitance | Coss | _ | 44 | _ | pF | V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz |
| Reverse Transfer Capacitance | Crss | _ | 30 | _ | рF | 1 = 1.0IVID2 |
| Total Gate Charge | Q_g | _ | 2.3 | _ | nC | |
| Gate-Source Charge | Qgs | _ | 0.3 | _ | nC | $V_{DS} = 10V, I_D = 11.6A$ |
| Gate-Drain Charge | Q_{gd} | _ | 0.5 | _ | nC | |
| Turn-On Delay Time | t _{d(on)} | _ | 8 | _ | | |
| Rise Time | t _r | _ | 3.8 | _ | ns | $V_{DD} = 10V$, $R_L = 10\Omega$ |
| Turn-Off Delay Time | t _{d(off)} | _ | 19.6 | _ | 115 | $I_D = 1A$, $V_{GEN} = 4.5V$, $R_G = 6\Omega$ |
| Fall Time | t _f | | 8.3 | _ | | |

Notes:

- Device mounted on FR-4 PCB, or minimum recommended pad layout.
 Repetitive rating, pulse width limited by junction temperature.
 Short duration pulse test used to minimize self-heating effect.







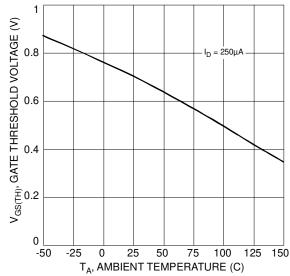
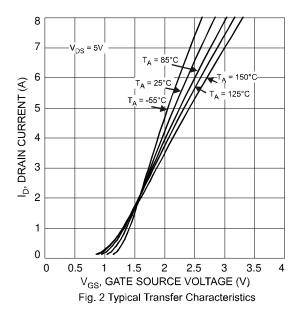


Fig. 5 Gate Threshold Variation with Temperature



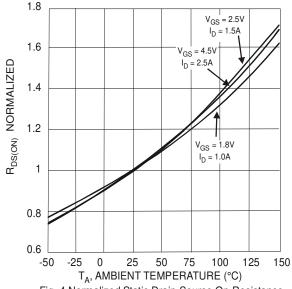
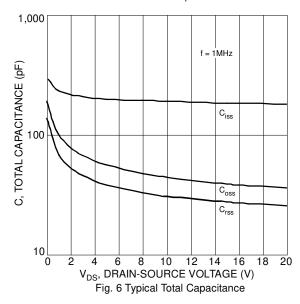
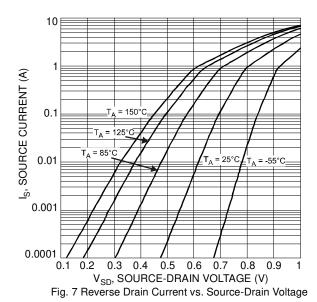
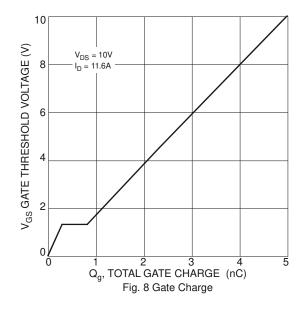


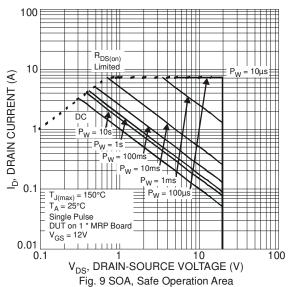
Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature





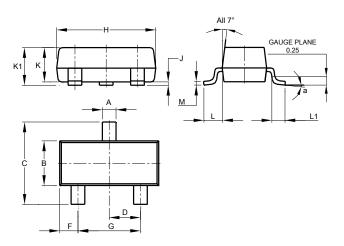






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

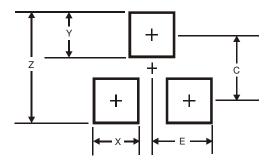


| SOT23 | | | | | | | |
|-------|--------|---------|-------|--|--|--|--|
| Dim | Min | Max | Тур | | | | |
| Α | 0.37 | 0.51 | 0.40 | | | | |
| В | 1.20 | 1.40 | 1.30 | | | | |
| С | 2.30 | 2.50 | 2.40 | | | | |
| D | 0.89 | 1.03 | 0.915 | | | | |
| F | 0.45 | 0.60 | 0.535 | | | | |
| G | 1.78 | 2.05 | 1.83 | | | | |
| Н | 2.80 | 3.00 | 2.90 | | | | |
| J | 0.013 | 0.10 | 0.05 | | | | |
| K | 0.890 | 1.00 | 0.975 | | | | |
| K1 | 0.903 | 1.10 | 1.025 | | | | |
| L | 0.45 | 0.61 | 0.55 | | | | |
| L1 | 0.25 | 0.55 | 0.40 | | | | |
| М | 0.085 | 0.150 | 0.110 | | | | |
| а | | 8° | | | | | |
| All | Dimens | ions in | mm | | | | |
| | | | | | | | |



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| Z | 2.9 |
| Х | 0.8 |
| Υ | 0.9 |
| С | 2.0 |
| E | 1.35 |

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